ANALOG DEVICES

Micropower, Dual-Channel Digital Isolators

Data Sheet

ADuM1240/ADuM1241/ADuM1245/ADuM1246

V_{DD1}

GND1(2)

NIC

NIC

VIB

FN₄

NIC

V_{IA}/V_{OA}

FEATURES

Ultralow power operation

3.3 V operation

5.6 µA per channel quiescent current, refresh enabled 0.3 µA per channel quiescent current, refresh disabled 148 µA/Mbps per channel typical dynamic current

2.5 V operation

3.1 µA per channel quiescent current, refresh enabled

0.1 µA per channel quiescent current, refresh disabled 116 µA/Mbps per channel typical dynamic current Small, 20-lead SSOP package and small 8-lead SOIC package **Bidirectional communication**

Up to 2 Mbps data rate nonreturn to zero (NRZ)

High temperature operation: 125°C

High common-mode transient immunity: >25 kV/µs

Safety and Regulatory Approvals

UL 1577 component recognition program 3750 V rms for 1 minute per UL 1577 (20-lead SSOP) 3000 V rms for 1 minute per UL 1577 (8-lead SOIC) **CSA Component Acceptance Notice 5A**

VDE certificate of conformity

DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 V_{IORM} = 849 V peak (20-lead SSOP)

V_{IORM} = 560 V peak (8-lead SOIC)

APPLICATIONS

General-purpose, low power, multichannel isolation 1 MHz low power serial peripheral interface (SPI) 4 mA to 20 mA loop process control

GENERAL DESCRIPTION

The ADuM1240/ADuM1241/ADuM1245/ADuM12461 are

micropower, 2-channel, digital isolators based on the Analog Devices, Inc., iCoupler[®] technology. Combining high speed, complementary metal oxide semiconductor (CMOS) and monolithic air core transformer technologies, these isolation components provide outstanding performance characteristics superior to the alternatives, such as optocoupler devices. The 20-lead SSOP version of the ADuM1240/ADuM1241/

ADuM1245/ADuM1246 allows control of the internal refresh functions. As shown in Figure 3, in standard operating mode, when $EN_x = 0$ (internal refresh enabled), the current per channel is less than 10 µA.

When $EN_x = 1$ (internal refresh disabled), the current per channel drops to less than 1 μ A.

¹ Protected by U.S. Patents 5,952,849, 6,873,065, 7,075,329, 6,262,600. Other patents pending.

(13) NIC н (12) NIC NIC || || (11) GND2 GND Figure 1. 20-Lead SSOP Package Functional Block Diagram V_{DD1} O ADuM124x (8) V_{DD2} VIA/VOA (2) ENCODE 38 DECODE .(6) V_{OB} GND₁((5) GND

ADuM124x

ENCODE

ENCODE

Figure 2. 8-Lead SOIC Package Functional Block Diagram

FUNCTIONAL BLOCK DIAGRAMS

35

П

20 V_{DD2}

(19) GND₂

(17) NIC

(15) V_{ов}

 $(14) EN_2$

DECODE

The ADuM1240/ADuM1241/ADuM1245/ADuM1246 are packaged in either a 20-lead SSOP for 3.75 kV reinforced isolation or an 8-lead SOIC for 3 kV basic isolation. The devices meet regulatory requirements, such as UL and CSA standards.

In addition to the space saving package options, the ADuM1240/ ADuM1241/ADuM1245/ADuM1246 operate with supplies as low as 2.25 V. All models provide low, pulse width distortion at <8 ns. In addition, every model has an input glitch filter to protect against extraneous noise disturbances.

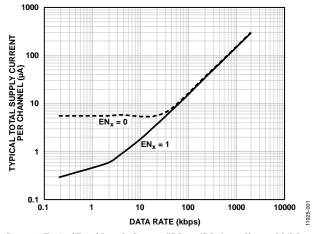


Figure 3. Typical Total Supply Current (IDD1 + IDD2) per Channel (VDDx = 3.3 V) as a Function of Data Rate

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Document Feedback

Rev. B

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REVISION HISTORY

9/2016-Rev. A to Rev. B

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3/2014—Rev. 0 to Rev. A

Added 8-lead SOIC Package	.Universal
Changes to Features Section, General Description Sec	tion, and
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12/2013—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—3.3 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = V_{DD2} = 3.3$ V. Minimum and maximum specifications apply over the entire recommended operation range of 3.0 V $\leq V_{DD1} \leq 3.6$ V, 3.0 V $\leq V_{DD2} \leq 3.6$ V, and -40° C $\leq T_A \leq +125^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

Table 1.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Data Rate				2	Mbps	Within pulse width distortion (PWD) limit
Propagation Delay	t _{PHL} , t _{PLH}		80	180	ns	50% input to 50% output
Change vs. Temperature			200		ps/°C	
Minimum Pulse Width	PW	500			ns	Within PWD limit
Pulse Width Distortion	PWD			8	ns	tPlh - tPhl
Propagation Delay Skew ¹	t _{PSK}			10	ns	
Channel Matching						
Codirectional	t _{PSKCD}			10	ns	
Opposing Direction	t pskod			15	ns	

¹ t_{PSK} is the magnitude of the worst case difference in t_{PHL} and t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

Table 2.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SUPPLY CURRENT						2 Mbps, no load
ADuM1240/ADuM1245	I _{DD1}		366	600	μΑ	
	I _{DD2}		246	375	μΑ	
ADuM1241/ADuM1246	I _{DD1}		306	450	μΑ	
	I _{DD2}		306	450	μΑ	

Table 3.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
Input Threshold						
Logic High	VIH	0.7 V _{DDx} ¹			V	
Logic Low	VIL			$0.3 V_{DDx}^{1}$	V	
Output Voltages						
Logic High	V _{OH}	$V_{DDx}^{1} - 0.1$	3.3		V	$I_{OUTx} = -20 \ \mu A, V_{Ix} = V_{IxH}$
		$V_{DDx}^1 - 0.4$	3.1		V	$I_{OUTx} = -4 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low	V _{OL}		0.0	0.1	V	$I_{OUTx} = 20 \ \mu A$, $V_{Ix} = V_{IxL}$
			0.2	0.4	V	$I_{OUTx} = 4 \text{ mA}, V_{Ix} = V_{IxL}$
Input Current per Channel	-li	-1	+0.01	+1	μA	$0 V \leq V_{lx} \leq V_{DDx}^{1}$
Input Switching Thresholds						
Positive Threshold Voltage	V_{T+}		1.8		V	
Negative Going Threshold	V _{T-}		1.2		V	
Input Hysteresis	ΔV_T		0.6		V	
Undervoltage Lockout, VDD1 or VDD2	UVLO		1.5		V	
Supply Current per Channel						
Quiescent Current						
Input Supply	I _{DDI (Q)}		4.8	10	μA	EN _x low
Output Supply	IDDO (Q)		0.8	6	μA	EN _x low
Input (Refresh Off)	I _{DDI (Q)}		0.12		μA	EN _x high
Output (Refresh Off)	I _{DDO (Q)}		0.13		μA	EN _x high

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
Dynamic Supply Current						
Input	DDI (D)		88		µA/Mbps	
Output	IDDO (D)		60		µA/Mbps	
AC SPECIFICATIONS						
Output Rise Time/Fall Time	t _R /t _F		2		ns	10% to 90%
Common-Mode Transient Immunity ²	CM	25	40		kV/μs	$V_{1x} = V_{DDx}^{1}$, $V_{CM} = 1000 V$, transient magnitude = 800 V
Refresh Rate	fr		14		kbps	

¹ $V_{DDx} = V_{DD1}$ or V_{DD2} .

 2 [CM] is the maximum common-mode voltage slew rate that can be sustained while maintaining V_{OUT} > 0.8 V_{DDw}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

ELECTRICAL CHARACTERISTICS—2.5 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = V_{DD2} = 2.5$ V. Minimum and maximum specifications apply over the entire recommended operation range of 2.25 V $\leq V_{DD1} \leq 2.75$ V, 2.25 V $\leq V_{DD2} \leq 2.75$ V, and -40° C $\leq T_A \leq +125^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

Table 4.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Data Rate				2	Mbps	Within PWD limit
Propagation Delay	tphl, tplh		112	180	ns	50% input to 50% output
Change vs. Temperature			280		ps/°C	
Pulse Width Distortion	PWD			12	ns	tplh — tphl
Minimum Pulse Width	PW	500			ns	Within PWD limit
Propagation Delay Skew ¹	t _{PSK}			10	ns	
Channel Matching						
Codirectional	t _{PSKCD}			10	ns	
Opposing Direction	t _{PSKOD}			30	ns	

¹ t_{PSK} is the magnitude of the worst case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

Table 5.

Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions/Comments
SUPPLY CURRENT						2 Mbps, no load
ADuM1240/ADuM1245	I _{DD1}		312	400	μA	
	I _{DD2}		168	250	μΑ	
ADuM1241/ADuM1246	I _{DD1}		240	375	μΑ	
	I _{DD2}		240	375	μΑ	

Table 6.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
Input Threshold						
Logic High	VIH	0.7 V _{DDx} ¹			V	
Logic Low	VIL			$0.3 V_{DDx}^{1}$	V	
Output Voltages						
Logic High	Vон	$V_{DDx}^1 - 0.1$	2.5		V	$I_{Ox} = -20 \ \mu A, V_{Ix} = V_{IxH}$
		$V_{DDx}^1 - 0.4$	2.35		V	$I_{Ox} = -4 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low	Vol		0.0	0.1	V	$I_{Ox} = 20 \ \mu A, V_{Ix} = V_{IxL}$
			0.1	0.4	V	$I_{Ox} = 4 \text{ mA}, V_{Ix} = V_{IxL}$
Input Current per Channel	h	-1	+0.01	+1	μA	$0V \leq V_{lx} \leq V_{DDx}{}^1$
Input Switching Thresholds						
Positive Threshold Voltage	V_{T+}		1.5		V	
Negative Going Threshold	V _{T-}		1.0		V	
Input Hysteresis	ΔV_{T}		0.5		V	
Undervoltage Lockout, V _{DD1} or V _{DD2}	UVLO		1.5		V	
Supply Current per Channel						
Quiescent Current						
Input Supply	IDDI (Q)		2.6	3.75	μΑ	EN _x low
Output Supply	I _{DDO (Q)}		0.5	3.75	μA	EN _x low
Input (Refresh Off)	IDDI (Q)		0.05		μA	EN _x high
Output (Refresh Off)	I _{DDO (Q)}		0.05		μA	EN _x high
Dynamic Supply Current						
Input	IDDI (D)		76		µA/Mbps	
Output	IDDO (D)		41		µA/Mbps	
AC SPECIFICATIONS						
Output Rise Time/Fall Time	t _R /t _F		2		ns	10% to 90%
Common-Mode Transient Immunity ²	CM	25	40		kV/μs	$V_{lx} = V_{DDx}^{1}, V_{CM} = 1000 V,$
						transient magnitude = 800 V
Refresh Rate	fr		14		kbps	

 1 V_{DDx} = V_{DD1} or V_{DD2}. 2 [CM] is the maximum common-mode voltage slew rate that can be sustained while maintaining V_{OUT} > 0.8 V_{DDx}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

ELECTRICAL CHARACTERISTICS-V_{DD1} = 3.3 V, V_{DD2} = 2.5 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = 3.3$ V, and $V_{DD2} = 2.5$ V. Minimum and maximum specifications apply over the entire recommended operation range of 3.0 V $\leq V_{DD1} \leq 3.6$ V, 2.25 V $\leq V_{DD2} \leq 2.75$ V, and -40° C $\leq T_A \leq +125^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

For dc specifications and ac specifications, see Table 3 for parameters related to Side 1 operation, and see Table 6 for parameters related to Side 2 operation.

Table 7.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Data Rate				2	Mbps	Within PWD limit
Propagation Delay						
Side 1 to Side 2	tphl, tplh		84	180	ns	50% input to 50% output
Side 2 to Side 1	tphl, tplh		120	180	ns	50% input to 50% output
Change vs. Temperature			280		ps/°C	
Pulse Width Distortion	PWD			12	ns	tplh — tphl
Pulse Width	PW	500			ns	Within PWD limit
Propagation Delay Skew ¹	t PSK			10	ns	
Channel Matching						
Codirectional	t pskcd			10	ns	
Opposing Direction	t _{PSKOD}			60	ns	

¹ t_{PSK} is the magnitude of the worst case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions. **Table 8.**

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SUPPLY CURRENT						2 Mbps, no load
ADuM1240/ADuM1245	I _{DD1}		366	500	μA	
	I _{DD2}		168	375	μA	
ADuM1241/ADuM1246	I _{DD1}		306	400	μA	
	I _{DD2}		240	375	μA	

ELECTRICAL CHARACTERISTICS—V_{DD1} = 2.5 V, V_{DD2} = 3.3 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = 2.5$ V, and $V_{DD2} = 3.3$ V. Minimum and maximum specifications apply over the entire recommended operation range of 2.25 V $\leq V_{DD1} \leq 2.75$ V, 3.0 V $\leq V_{DD2} \leq 3.6$ V, and -40° C $\leq T_A \leq +125^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

For dc specifications and ac specifications, see Table 6 for parameters related to Side 1 operation, and see Table 3 for parameters related to Side 2 operation.

Table 9.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Data Rate				2	Mbps	Within PWD limit
Propagation Delay						
Side 1 to Side 2	t _{PHL} , t _{PLH}		120	180	ns	50% input to 50% output
Side 2 to Side 1	t _{PHL} , t _{PLH}		84	180	ns	50% input to 50% output
Change vs. Temperature			200		ps/°C	
Pulse Width Distortion	PWD			12	ns	tplh - tphl
Pulse Width	PW	500			ns	Within PWD limit
Propagation Delay Skew ¹	t _{PSK}			10	ns	
Channel Matching						
Codirectional	t PSKCD			10	ns	
Opposing Direction	t pskod			60	ns	

¹ t_{PSK} is the magnitude of the worst case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

Table 10.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
SUPPLY CURRENT						2 Mbps, no load
ADuM1240/ADuM1245	I _{DD1}		306	500	μA	
	I _{DD2}		248	375	μA	
ADuM1241/ADuM1246	I _{DD1}		240	375	μA	
	I _{DD2}		306	450	μΑ	

PACKAGE CHARACTERISTICS

Table 11.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions/Comments
Resistance (Input to Output) ¹	RI-0		10 ¹³		Ω	
Capacitance (Input to Output) ¹	CI-O		2		рF	f = 1 MHz
Input Capacitance ²	Cı		4.0		рF	
IC Junction to Ambient Thermal Resistance	ALθ		85		°C/W	Thermocouple located at center of package underside

¹ The device is considered a 2-terminal device: Pin 1 through Pin 8 are shorted together, and Pin 9 through Pin 16 are shorted together.

² Input capacitance is from any input data pin to ground.

REGULATORY INFORMATION

See Table 18 and the Absolute Maximum Ratings section for recommended maximum working voltages for specific cross isolation waveforms and insulation levels.

Table 12.

UL	CSA	VDE
Recognized under 1577 component recognition program ¹	Approved under CSA Component Acceptance Notice 5A	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 ²
Single protection, 8-lead SOIC package, 3000 V rms isolation voltage	8-lead SOIC package, basic insulation per CSA 60950-1-03 and IEC 60950-1, 400 V rms (565 V peak) maximum working voltage	8-lead SOIC package, reinforced insulation, 560 V _{PEAK}
Single protection, 20-lead SSOP package, 3750 V rms isolation voltage	20-lead SSOP package, basic insulation per CSA 60950-1-03 and IEC 60950-1, 530 V rms (700 V peak) maximum working voltage	20-lead SSOP package, reinforced insulation, 849 V _{PEAK}
	20-lead SSOP package, reinforced insulation per CSA 60950-1-03 and IEC 60950-1, 265 V rms (374 V peak) maximum working voltage	
File E214100	File 205078	File 2471900-4880-0001

¹ In accordance with UL1577, each ADuM1240/ADuM1241/ADuM1245/ADuM1246 is proof tested by applying an insulation test voltage \geq 3000 V rms for 1 second (current leakage detection limit = 5 µA).

² In accordance with DIN V VDE V 0884-10, each ADuM1240/ADuM1241/ADuM1245/ADuM1246 is proof tested by applying an insulation test voltage ≥1050 V peak for 1 second (partial discharge detection limit = 5 pC). The asterisk (*) marked on the component designates DIN V VDE V 0884-10 approval.

INSULATION AND SAFETY RELATED SPECIFICATIONS

Table 13.

Parameter	Symbol	Value	Unit	Test Conditions/Comments
Rated Dielectric Insulation Voltage (8-Lead SOIC)		3000	V rms	1 minute duration
Rated Dielectric Insulation Voltage (20-Lead SSOP)		3750	V rms	1 minute duration
Minimum External Tracking and Air Gap, 8-Lead SOIC (Creepage and Clearance)	L(102)	4	mm min	Measured from input terminals to output terminals, shortest distance path along package body
Minimum Clearance in the Plane of the Printed Circuit Board, 8-Lead SOIC (PCB Clearance)	L(I01)	4.5	mm min	Measured from input terminals to output terminals, shortest distance through air, line of sight, in the PCB mounting plane
Minimum Clearance in the Plane of the Printed Circuit Board, 20-Lead SSOP (PCB Clearance)	L(I01)	5.1	mm min	Measured from input terminals to output terminals, shortest distance path along package body
Minimum Clearance in the Plane of the Printed Circuit Board, 20-Lead SSOP (PCB Clearance)	L(I02)	5.1	mm min	Measured from input terminals to output terminals, shortest distance through air, line of sight, in the PCB mounting plane
Minimum Internal Gap (Internal Clearance)		0.017	mm min	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	СТІ	>400	V	DIN IEC 112/VDE 0303 Part 1
Isolation Group		П		Material Group (DIN VDE 0110, 1/89, Table 1)

DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 INSULATION CHARACTERISTICS

These isolators are suitable for reinforced electrical isolation within the safety limit data only. Maintenance of the safety data is ensured by protective circuits. The asterisk (*) marked on packages denotes DIN V VDE V 0884-10 approval.

Table 14. 8-Lead SOIC (R-8)

Parameter	Symbol	Test Conditions/Comments	Characteristic	Unit
Installation Classification per DIN VDE 0110				
For Rated Mains Voltage ≤ 150 V rms			l to IV	
For Rated Mains Voltage ≤ 300 V rms			l to III	
For Rated Mains Voltage ≤ 400 V rms			l to ll	
Climatic Classification			40/105/21	
Pollution Degree per DIN VDE 0110, Table 1			2	
Maximum Working Insulation Voltage	VIORM		560	VPEAK
Input to Output Test Voltage, Method b1	$V_{pd(m)}$	$V_{IORM} \times 1.875 = V_{pd(m)}$, 100% production test, $t_{ini} = t_m =$ one second, partial discharge < 5 pC	1050	V _{PEAK}
Input to Output Test Voltage, Method a				
After Environmental Tests Subgroup 1	$V_{pd(m)}$	$V_{IORM} \times 1.5 = V_{pd(m)}$, $t_{ini} = 60$ seconds, $t_m = 10$ seconds, partial discharge < 5 pC	840	Vpeak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{pd(m)}$	$V_{IORM} \times 1.2 = V_{pd(m)}$, $t_{ini} = 60$ seconds, $t_m = 10$ seconds, partial discharge < 5 pC	672	Vpeak
Highest Allowable Overvoltage	VIOTM		3500	VPEAK
Surge Isolation Voltage	VIOSM	$V_{PEAK} = 10$ kV, 1.2 µs rise time, 50 µs, 50% fall time	4000	VPEAK
Safety Limiting Values		Maximum value allowed in the event of a failure (see Figure 4)		
Case Temperature	Ts		150	°C
Total Power Dissipation at 25°C	I _{S1}		1.64	W
Insulation Resistance at Ts	Rs	$V_{10} = 500 V$	>109	Ω

Table 15. 20-Lead SSOP (RS-20)

Parameter	Symbol	Test Conditions/Comments	Characteristic	Unit
Installation Classification per DIN VDE 0110				
For Rated Mains Voltage ≤ 150 V rms			l to IV	
For Rated Mains Voltage ≤ 300 V rms			l to III	
For Rated Mains Voltage ≤ 400 V rms			l to ll	
Climatic Classification			40/105/21	
Pollution Degree per DIN VDE 0110, Table 1			2	
Maximum Working Insulation Voltage	VIORM		849	VPEAK
Input to Output Test Voltage, Method b1	$V_{pd(m)}$	$ V_{\text{IORM}} \times 1.875 = V_{\text{pd(m)}}, 100\% \text{ production test}, \\ t_{\text{ini}} = t_m = \text{one second, partial discharge} < 5 \text{ pC} $	1592	V _{PEAK}
Input to Output Test Voltage, Method a				
After Environmental Tests Subgroup 1	$V_{pd(m)}$	$V_{IORM} \times 1.5 = V_{pd(m)}$, $t_{ini} = 60$ seconds, $t_m = 10$ seconds, partial discharge < 5 pC	1273	V _{PEAK}
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{pd(m)}$	$V_{IORM} \times 1.2 = V_{pd(m)}$, $t_{ini} = 60$ seconds, $t_m = 10$ seconds, partial discharge < 5 pC	1018	V _{PEAK}
Highest Allowable Overvoltage	VIOTM		5335	VPEAK
Surge Isolation Voltage	VIOSM	$V_{PEAK} = 10$ kV, 1.2 μ s rise time, 50 μ s, 50% fall time	6000	Vpeak
Safety Limiting Values		Maximum value allowed in the event of a failure (see Figure 4)		
Case Temperature	Ts		150	°C
Side 1 IDD1 Current	I _{S1}		2.5	W
Insulation Resistance at Ts	Rs	$V_{IO} = 500 V$	>109	Ω

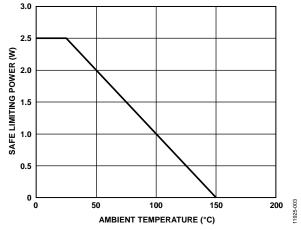


Figure 4. Thermal Derating Curve, Dependent on Safety Limiting Values with Ambient Temperature per DIN V VDE V 0884-10

RECOMMENDED OPERATING CONDITIONS

Table 16.

Parameter	Symbol	Min	Max	Unit
Operating Temperature	TA	-40	+125	°C
Supply Voltages ¹	V_{DD1}, V_{DD2}	2.25	3.6	V
Input Signal Rise and Fall Times			1.0	ms

 $^{\rm 1}$ See the DC Correctness and Low Power Operation section for more information.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25^{\circ}C$, unless otherwise noted.

Table 17.

Parameter	Rating		
Storage Temperature (T _{ST}) Range	–65°C to +150°C		
Ambient Operating Temperature (T _A) Range	–40°C to +125°C		
Supply Voltages (V _{DD1} , V _{DD2})	–0.5 V to +5 V		
Input Voltages (V _{IA} , V _{IB})	-0.5 V to V _{DDI} + 0.5 V		
Output Voltages (Voa, Vob)	-0.5 V to V _{DD2} + 0.5 V		
Average Output Current per Pin ¹			
Side 1 (I ₀₁)	-10 mA to +10 mA		
Side 2 (I _{O2})	-10 mA to +10 mA		
Common-Mode Transients ²	–100 kV/µs to +100 kV/µs		

¹ See Figure 4 for maximum rated current values for various temperatures.
² Refers to common-mode transients across the insulation barrier. Common-mode transients exceeding the absolute maximum ratings can cause latch-up or permanent damage.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

CONTINUOUS WORKING VOLTAGE

Table 18. Maximum Continuous Working Voltage¹

Parameter	Max	Unit	Constraint
AC Voltage			
Bipolar Waveform	565	V peak	50-year minimum lifetime
Unipolar Waveform	1131	V peak	50-year minimum lifetime
DC Voltage	1131	V peak	50-year minimum lifetime

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

V_{DD1} 1 GND₁ 2

NIC 3

NIC 4

V_{IA} 5

V_{IB} 6

EN₁7 NIC 8

NIC 9

GND1 10

20 V_{DD2}

19 GND₂

18 NIC

17 NIC

16 V_{OA}

15 V_{OB} 14 EN₂

13 NIC

12 NIC

11 GND₂

1925

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



Figure 5. ADuM1240/ADuM1245 8-Lead SOIC (R-8) Pin Configuration

NIC = NOT INTERNALLY CONNECTED. Figure 6. ADuM1240/ADuM1245 20-Lead SSOP (RS-20) Pin Configuration

ADuM1240/

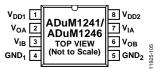
ADuM1245 TOP VIEW (Not to Scale)

8-Lead SOIC Pin No. ²	20-Lead SSOP Pin No.	Mnemonic	Description
1	1	V _{DD1}	Supply Voltage for Isolator Side 1 (2.25 V to 3.6 V). Connect a ceramic bypass capacitor in the range of 0.01 μ F to 0.1 μ F between V _{DD1} and GND ₁ .
N/A	2	GND1	Ground 1. Ground reference for Isolator Side 1. Pin 2 and Pin 10 are internally connected, and connecting both to GND1 is recommended.
N/A	3	NIC	Not Internally Connected. Leave this pin floating.
N/A	4	NIC	Not Internally Connected. Leave this pin floating.
2	5	VIA	Logic Input A.
3	6	VIB	Logic Input B.
N/A	7	EN1	Refresh and Watchdog Enable 1. In the 20-lead SSOP package, connecting Pin 7 to GND ₁ enables the input/output refresh and watchdog functionality for Side 1, supporting standard <i>i</i> Coupler operation. Tying Pin 7 to V _{DD1} disables the refresh and watchdog functionality for the lowest power operation. See the DC Correctness and Low Power Operation section for a description of this mode. EN ₁ and EN ₂ must be set to the same logic state.
N/A	8	NIC	Not Internally Connected. Leave this pin floating.
N/A	9	NIC	Not Internally Connected. Leave this pin floating.
4	10	GND1	Ground 1. Ground reference for Isolator Side 1. In the 20-lead SSOP package, Pin 2 and Pin 10 are internally connected, and connecting both to GND1 is recommended.
5	11	GND ₂	Ground 2. Ground reference for Isolator Side 2. In the 20-lead SSOP package, Pin 11 and Pin 19 are internally connected, and connecting both to GND ₂ is recommended.
N/A	12	NIC	Not Internally Connected. Leave this pin floating.
N/A	13	NIC	Not Internally Connected. Leave this pin floating.
N/A	14	EN ₂	Refresh and Watchdog Enable 2. In the 20-lead SSOP package, connecting Pin 14 to GND ₂ enables the input/output refresh and watchdog functionality for Side 2, supporting standard <i>i</i> Coupler operation. Tying Pin 14 to V_{DD2} disables the refresh and watchdog functionality for lowest power operation. See the DC Correctness and Low Power Operation section for a description of this mode. EN1 and EN2 must be set to the same logic state.
6	15	V _{OB}	Logic Output B.
7	16	Voa	Logic Output A.
N/A	17	NIC	Not Internally Connected. Leave this pin floating.
N/A	18	NIC	Not Internally Connected. Leave this pin floating.
N/A	19	GND ₂	Ground 2. Ground reference for Isolator Side 2. In the 20-lead SSOP package, Pin 11 and Pin 19 are internally connected, and connecting both to GND ₂ is recommended.
8	20	V _{DD2}	Supply Voltage for Isolator Side 2 (2.25 V to 3.6 V). Connect a ceramic bypass capacitor in the range of 0.01 μ F to 0.1 μ F between V _{DD2} and GND ₂ .

Table 19. ADuM1240/ADuM1245 8-Lead SOIC (R-8) and 20-Lead SSOP (RS-20) Pin Function Descriptions¹

¹ Reference AN-1109 for specific layout guidelines.

² N/A means not applicable.



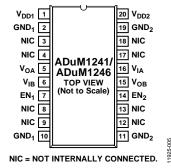


Figure 7. ADuM1241/ADuM1246 8-Lead SOIC (R-8) Pin Configuration

Figure 8. ADuM1241/ADuM1246 20-Lead SSOP (RS-20) Pin Configuration

Table 20. ADuM1241/ADuM1246 8-Lead SOIC (R-8) and 20-Lead SSOP (RS-20) Pin Function Descriptions¹

8-Lead	20-Lead		
SOIC Pin No. ²	SSOP Pin No.	Mnemonic	Description
1	1	V _{DD1}	Supply Voltage for Isolator Side 1 (2.25 V to 3.6 V). Connect a ceramic bypass capacitor in the range of 0.01 μ F to 0.1 μ F between V _{DD1} and GND ₁ .
N/A	2	GND1	Ground 1. Ground reference for Isolator Side 1. Pin 2 and Pin 10 are internally connected, and connecting both to GND ₁ is recommended.
N/A	3	NIC	Not Internally Connected. Leave this pin floating.
N/A	4	NIC	Not Internally Connected. Leave this pin floating.
2	5	Voa	Logic Output A.
3	6	VIB	Logic Input B.
N/A	7	EN1	Refresh and Watchdog Enable 1. In the 20-lead SSOP package, connecting Pin 7 to GND ₁ enables the input/output refresh and watchdog functionality for Side 1, supporting standard <i>i</i> Coupler operation. Tying Pin 7 to V _{DD1} disables the refresh and watchdog functionality for the lowest power operation. See the DC Correctness and Low Power Operation section for a description of this mode. EN ₁ and EN ₂ must be set to the same logic state.
N/A	8	NIC	Not Internally Connected. Leave this pin floating.
N/A	9	NIC	Not Internally Connected. Leave this pin floating.
4	10	GND ₁	Ground 1. Ground reference for Isolator Side 1. In the 20-lead SSOP package, Pin 2 and Pin 10 are internally connected, and connecting both to GND_1 is recommended.
5	11	GND ₂	Ground 2. Ground reference for Isolator Side 2. In the 20-lead SSOP package, Pin 11 and Pin 19 are internally connected, and connecting both to GND_2 is recommended.
N/A	12	NIC	Not Internally Connected. Leave this pin floating.
N/A	13	NIC	Not Internally Connected. Leave this pin floating.
N/A	14	EN ₂	Refresh and Watchdog Enable 2. In the 20-lead SSOP package, connecting Pin 14 to GND ₂ enables the input/output refresh and watchdog functionality for Side 2, supporting standard <i>i</i> Coupler operation. Tying Pin 14 to V_{DD2} disables the refresh and watchdog functionality for lowest power operation. See the DC Correctness and Low Power Operation section for a description of this mode. EN1 and EN2 must be set to the same logic state.
6	15	V _{OB}	Logic Output B.
7	16	VIA	Logic Input A.
N/A	17	NIC	Not Internally Connected. Leave this pin floating.
N/A	18	NIC	Not Internally Connected. Leave this pin floating.
N/A	19	GND ₂	Ground 2. Ground reference for Isolator Side 2. In the 20-lead SSOP package, Pin 11 and Pin 19 are internally connected, and connecting both to GND_2 is recommended.
8	20	V _{DD2}	Supply Voltage for Isolator Side 2 (2.25 V to 3.6 V). Connect a ceramic bypass capacitor in the range of 0.01 μ F to 0.1 μ F between V _{DD2} and GND ₂ .

¹ Reference AN-1109 for specific layout guidelines.

 $^{\rm 2}$ N/A means not applicable.

Table 21. Truth Table Abbreviations

TRUTH TABLES

Table 22 provides the truth table (positive logic) for the ADuM1240 and the ADuM1241, and Table 23 provides the truth table (positive logic) for the ADuM1245 and the ADuM1246. For a description of the abbreviations used in the truth tables, see Table 21.

Letter	Description						
Н	High level						
L	Low level						
\uparrow	Rising data transition						
\downarrow	Falling data transition						
Х	Irrelevant						
Qo	Level of Vox prior to levels being established						
Z	High impedance						

			ENx			
V _{ix} Input	V _{DDI} State	V _{DDO} State	State	V _{ox} Output	Description	
Н	Powered	Powered	L	Н	Normal operation; data is high and refresh is enabled.	
L	Powered	Powered	L	L	Normal operation; data is low and refresh is enabled.	
Х	Unpowered	Powered	L	H Input unpowered. Outputs are in the default high state. Outputs re the input state within 150 μ s of V _{DDI} power restoration. See the pin fu descriptions (Table 19 and Table 20) for details.		
Х	Unpowered	Powered	Н	Qo	Input unpowered. Outputs are static at the level that was last sent from the input or at the power-up level. See the pin function descriptions (Table 19 and Table 20) for details.	
	Powered	Powered	Н	н	Output is high after propagation delay, refresh is disabled.	
	Powered	Powered	н	L	Output is low after propagation delay, refresh is disabled.	
Х	Powered	Unpowered	Х	Z	Output unpowered. Output pins are in high impedance state. Outputs return to the input state within 150 μ s of V _{DDO} power restoration. See the pin function descriptions (Table 19 and Table 20) for details.	

Table 22. ADuM1240/ADuM1241 Truth Table (Positive Logic)^{1, 2, 3}

 $^1\,V_{\rm lx}$ and $V_{\rm Ox}$ refer to the input and output signals of a given channel (A, B, C, or D).

 2 V_{DDI} refers to the power supply on the input side of a given channel (A, B, C, or D).

 3 V_{DDO} refers to the power supply on the output side of a given channel (A, B, C, or D).

Table 23. ADuM1245/ADuM1246 Truth Table (Positive Logic)^{1, 2, 3}

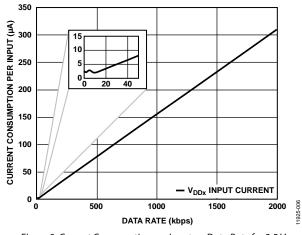
V _{Ix} Input	V _{DDI} State	V _{DDO} State	EN _x State	Vox Output	Description			
Н	Powered	Powered	L	Н	Normal operation; data is high and refresh is enabled.			
L	Powered	Powered	L	L	Normal operation; data is low and refresh is enabled.			
Х	Unpowered	Powered	L	L	Input unpowered. Outputs are in the default low state. Outputs return to the input state within 150 μ s of V _{DDI} power restoration. So the pin function descriptions (Table 19 and Table 20) for details.			
Х	Unpowered	Powered	н	Qo	Input unpowered. Outputs are static at the level that was last sent from the input or at the power-up level. See the pin function descriptions (Table 19 and Table 20) for details.			
	Powered	Powered	н	н	Output is high, refresh is disabled.			
	Powered	Powered	н	L	Output is low, refresh is disabled.			
Х	Powered	Unpowered	x	Z	Output unpowered. Output pins are in high impedance state. Outputs return to input state within 150 μ s of V _{DDO} power restoration. See the pin function descriptions (Table 19 and Table 20) for details.			

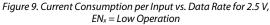
 $^1\,V_{lx}$ and V_{0x} refer to the input and output signals of a given channel (A, B, C, or D).

 $^2\,V_{\text{DDI}}$ refers to the power supply on the input side of a given channel (A, B, C, or D).

 3 V_{DDO} refers to the power supply on the output side of a given channel (A, B, C, or D).

TYPICAL PERFORMANCE CHARACTERISTICS





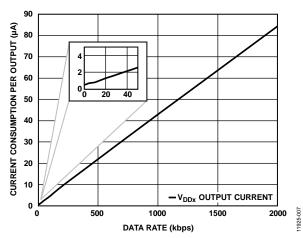


Figure 10. Current Consumption per Output vs. Data Rate for 2.5 V, EN_x = Low Operation

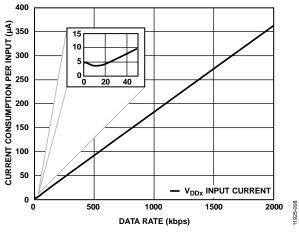


Figure 11. Current Consumption per Input vs. Data Rate for 3.3 V, EN_x = Low Operation

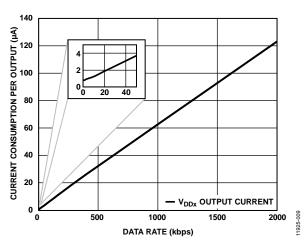


Figure 12. Current Consumption per Output vs. Data Rate for 3.3 V, EN_x = Low Operation

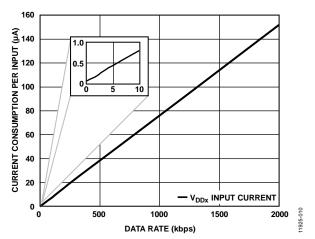


Figure 13. Current Consumption per Input vs. Data Rate for 2.5 V, $EN_x = High Operation$

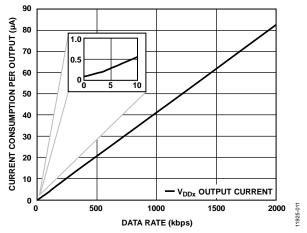
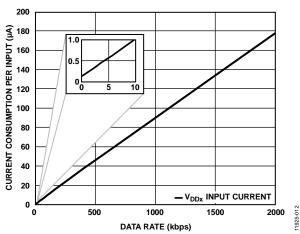
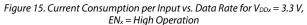


Figure 14. Current Consumption per Output vs. Data Rate for 2.5 V, EN_x = High Operation





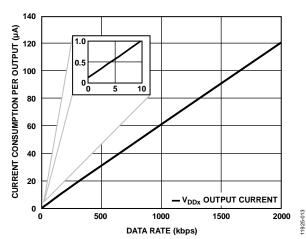


Figure 16. Current Consumption per Output vs. Data Rate for $V_{DDx} = 3.3 V$, EN_x = High Operation

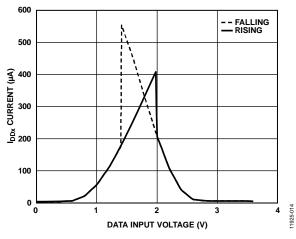


Figure 17. Typical I_{DDx} Current per Input vs. Data Input Voltage for $V_{DDx} = 3.3 V$

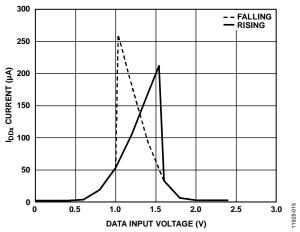


Figure 18. I_{DDx} Current per Input vs. Data Input Voltage for $V_{DDx} = 2.5 V$

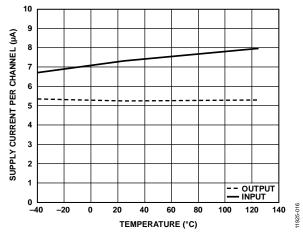


Figure 19. Typical Input and Output Supply Current per Channel vs. Temperature for $V_{DDx} = 2.5 V$, Data Rate = 100 kbps

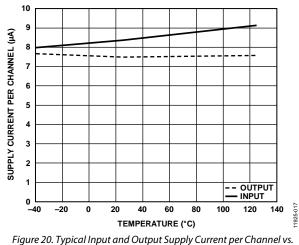


Figure 20. Typical Input and Output Supply Current per Channel vs. Temperature for $V_{DDx} = 3.3 V$, Data Rate = 100 kbps

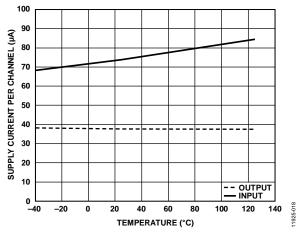


Figure 21. Typical Input and Output Supply Current per Channel vs. Temperature for $V_{DDX} = 2.5 V$, Data Rate = 1000 kbps

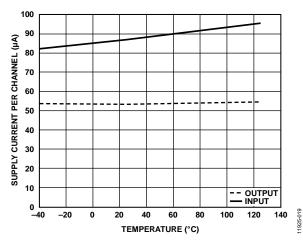


Figure 22. Typical Input and Output Supply Current per Channel vs. Temperature for V_{DDX} = 3.3 V, Data Rate = 1000 kbps

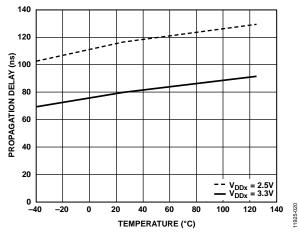


Figure 23. Typical Propagation Delay vs. Temperature for $V_{DDx} = 3.3$ V or $V_{DDx} = 2.5$ V

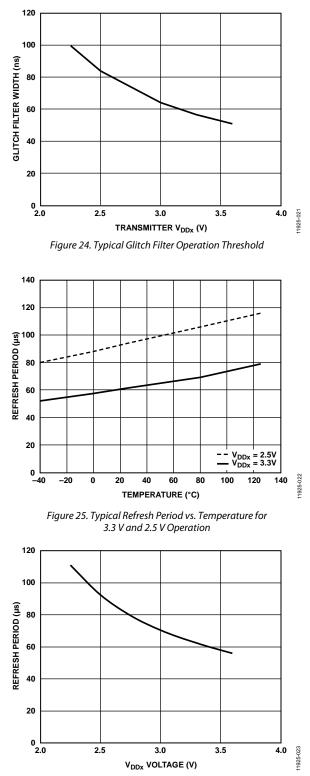


Figure 26. Typical Refresh Period vs. V_{DDx} Voltage

APPLICATIONS INFORMATION PCB LAYOUT

The ADuM1240/ADuM1241/ADuM1245/ADuM1246 digital isolators require no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at both the input and output supply pins: V_{DD1} and V_{DD2} (see Figure 27). Maintain the capacitor value between 0.01 μ F and 0.1 μ F and for best results, ensure that the total lead length between both ends of the capacitor and the input power supply does not exceed 20 mm.

With proper PCB design choices, these digital isolators readily meet CISPR 22 Class A (and FCC Class A) emissions standards, as well as the more stringent CISPR 22 Class B (and FCC Class B) standards in an unshielded environment. Refer to AN-1109 for PCB related electromagnetic interference (EMI) mitigation techniques, including board layout and stack up issues.

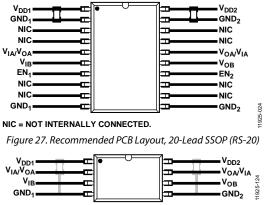
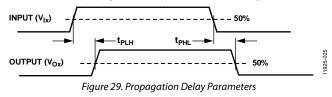


Figure 28. Recommended PCB Layout, 8-Lead SOIC (R-8)

For applications involving high common-mode transients, it is important to minimize board coupling across the isolation barrier. Furthermore, design the board layout so that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this equal capacitive coupling of pins can cause voltage differentials between pins exceeding the absolute maximum ratings of the device, thereby leading to latch-up or permanent damage.

PROPAGATION DELAY RELATED PARAMETERS

Propagation delay is a parameter that describes the time it takes a logic signal to propagate through a component. The input to output propagation delay time for a high to low transition can differ from the propagation delay time of a low to high transition.



Pulse width distortion is the maximum difference between these two propagation delay values, and an indication of how accurately the timing of the input signal is preserved. Channel to channel matching refers to the maximum amount the propagation delay differs between channels within a single component of the ADuM1240/ADuM1241/ADuM1245/ ADuM1246.

Propagation delay skew refers to the maximum amount the propagation delay differs between multiple ADuM1240/ ADuM1241/ADuM1245/ADuM1246 components operating under the same conditions.

DC CORRECTNESS AND LOW POWER OPERATION Standard Operating Mode

Positive and negative logic transitions at the isolator input cause narrow (~1 ns) pulses to be sent to the decoder using the transformer. The decoder is bistable and is, therefore, either set or reset by the pulses, indicating input logic transitions. When refresh and watchdog functions are enabled, by pulling EN_1 and EN_2 low, in the absence of logic transitions at the input for more than ~140 µs, a periodic set of refresh pulses, indicative of the correct input state, is sent to ensure dc correctness at the output. If the decoder receives no internal pulses of more than approximately 200 µs, the device assumes that the input side is unpowered or nonfunctional, in which case, the isolator watchdog circuit forces the output to a default state. The default state is either high, as in the ADuM1240 and ADuM1241 versions, or low, as in the ADuM1245 and ADuM1246 versions.

Low Power Operating Mode

For the lowest power consumption, disable the refresh and watchdog functions of the ADuM1240/ADuM1241/ADuM1245/ ADuM1246 by pulling $\rm EN_1$ and $\rm EN_2$ to logic high. These control pins must be set to the same value on each side of the component for proper operation.

In this mode, the current consumption of the chip drops to the microampere range. However, be careful when using this mode, because dc correctness is no longer guaranteed at startup. For example, if the following sequence of events occurs:

- 1. Power is applied to Side 1.
- 2. A high level is asserted on the V_{IA} input.
- 3. Power is applied to Side 2.

The high on V_{IA} is not automatically transferred to the Side 2 V_{OA} , and there can be a level mismatch that is not corrected until a transition occurs at V_{IA} . When power is stable on each side, and a transition occurs on the input of the channel, the input and output state of that channel is correctly matched. This contingency can be resolved in several ways, such as sending dummy data, or toggling refresh on for a short period to force synchronization after turn on.

Recommended Input Voltage for Low Power Operation

The ADuM1240/ADuM1241/ADuM1245/ADuM1246

implement Schmitt trigger input buffers so that the devices operate cleanly in low data rate, or in noisy environments. Schmitt triggers allow a small amount of shoot through current when the input voltage is not approximate to either V_{DDx} or GND_x levels. Shoot through is possible because the two transistors are both slightly on when input voltages are in the middle of the supply range. For many digital devices, this leakage is not a large portion of the total supply current and cannot be noticed; however, in the ultralow power

ADuM1240/ADuM1241/ADuM1245/ADuM1246, this leakage can be larger than the total operating current of the device and must not be ignored.

To achieve optimum power consumption with the ADuM1240/ ADuM1241/ADuM1245/ADuM1246, always drive the inputs as near to V_{DDx} or GND_x levels as possible. Figure 17 and Figure 18 illustrate the shoot through leakage of an input; therefore, whereas the logic thresholds of the input are standard CMOS levels, optimum power performance is achieved when the input logic levels are driven within 0.5 V of either V_{DDx} or GND_x levels.

MAGNETIC FIELD IMMUNITY

The limitation on the magnetic field immunity of the device is set by the condition in which, induced voltage in the transformer receiving coil is sufficiently large, to either falsely set or reset the decoder. The following analysis defines such conditions. The ADuM1240 is examined in a 3 V operating condition, because it represents the typical mode of operation for these products.

The pulses at the transformer output have an amplitude greater than 1.5 V. The decoder has a sensing threshold of about 1.0 V, therefore establishing a 0.5 V margin in which induced voltages are tolerated. The voltage induced across the receiving coil is given by

$$V = (-d\beta/dt) \sum \pi r_n^2; n = 1, 2, ..., N$$

where:

 β is the magnetic flux density.

 r_n is the radius of the n^{th} turn in the receiving coil. *N* is the number of turns in the receiving coil.

Given the geometry of the receiving coil in the ADuM1240, and an imposed requirement that the induced voltage be, at most, 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field is calculated as shown in Figure 30.

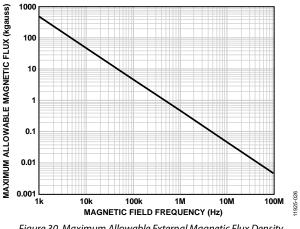
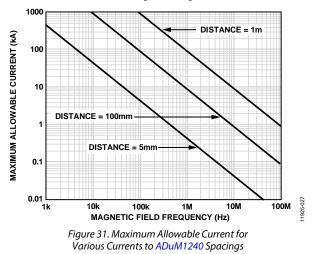


Figure 30. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.5 kgauss induces a voltage of 0.25 V at the receiving coil. This is about 50% of the sensing threshold and does not cause a faulty output transition. If such an event occurs, with the worst case polarity, during a transmitted pulse, it would reduce the received pulse from >1.0 V to 0.75 V. This is still higher than the 0.5 V sensing threshold of the decoder.

The preceding magnetic flux density values correspond to specific current magnitudes at given distances away from the ADuM1240 transformers. Figure 31 expresses these allowable current magnitudes as a function of frequency for selected distances. The ADuM1240 is very insensitive to external fields. Only extremely large, high frequency currents, very close to the component, could potentially be a concern. For the 1 MHz example noted, the user would have to place a 1.2 kA current 5 mm away from the ADuM1240 to affect component operation.



Note that at combinations of strong magnetic field and high frequency, any loops formed by PCB traces could induce sufficiently large error voltages to trigger the thresholds of succeeding circuitry. Avoid PCB structures that form loops.

POWER CONSUMPTION

The supply current with refresh enabled at a given channel of the ADuM1240/ADuM1241/ADuM1245/ADuM1246 isolators, is a function of the supply voltage, the data rate of the channel, and the output load of the channel.

For each input channel, the supply current is given by

I_{DDI}	$=I_{DDI(Q)}$				$f \le 0.5 f_r$
_	_		_		

$I_{DDI} = I_{DDI(D)} \times (2f - f_r) + I_{DDI(Q)}$	$f > 0.5 f_r$

For each output channel, the supply current is given by

$$I_{DDO} = I_{DDO(Q)} \qquad f \le 0.5 f_r$$

$$I_{DDO} = (I_{DDO(D)} + (0.5 \times 10^{-3}) \times C_L \times V_{DDO}) \times (2f - f_r) + I_{DDO(Q)}$$

 $f > 0.5 f_r$

where:

 $I_{DDI(D)}$ and $I_{DDO(D)}$ are the input and output dynamic supply currents per channel (mA/Mbps).

 C_L is the output load capacitance (pF).

 V_{DDO} is the output supply voltage (V).

f is the input logic signal frequency (MHz); it is half the input data rate, expressed in units of Mbps.

 f_r is the input stage refresh rate (Mbps) = $1/T_r$ (µs).

*I*_{DDI (Q)} and *I*_{DDO (Q)} are the specified input and output quiescent supply currents (mA).

To calculate the total V_{DD1} and V_{DD2} supply current, the supply currents for each input and output channel corresponding to V_{DD1} and V_{DD2} are calculated and totaled. Figure 9 through Figure 16 show per channel supply currents as a function of data rate for an unloaded output condition.

INSULATION LIFETIME

All insulation structures eventually degrade, when subjected to voltage stress for a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the

ADuM1240/ADuM1241/ADuM1245/ADuM1246.

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage.

ADuM1240/ADuM1241/ADuM1245/ADuM1246 The values shown in Table 18 summarize the peak voltage for 50

The values shown in Table 18 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition, and the maximum CSA/VDE approved working voltages. In many cases, the approved working voltage is higher than 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life, in some cases.

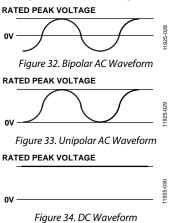
The insulation lifetime of the ADuM1240/ADuM1241/

ADuM1245/ADuM1246 depends on the voltage waveform type imposed across the isolation barrier. The *i*Coupler insulation structure degrades at different rates, depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 19, Figure 20, and Figure 21 illustrate these different isolation voltage waveforms.

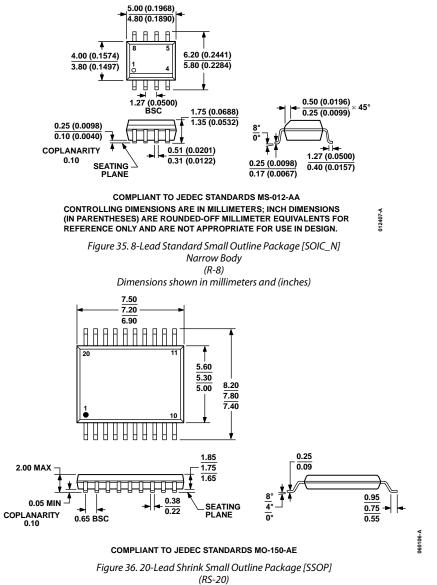
Bipolar ac voltage is the most stringent environment. The goal of a 50-year operating lifetime, under the ac bipolar condition, determines the Analog Devices recommended maximum working voltage.

In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower. This allows operation at higher working voltages, while still achieving a 50-year service life. The working voltages listed in Table 18 can be applied while maintaining the 50year minimum lifetime, provided the voltages conform to either the unipolar ac or dc voltage case. Treat any cross-insulation voltage waveform that does not conform to Figure 33 or Figure 34 as a bipolar ac waveform, and limit peak voltage to the 50-year lifetime voltage value listed in Table 18.

Note that the voltage presented in Figure 33 is shown as sinusoidal for illustration purposes only. It represents any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage must not cross 0 V.



OUTLINE DIMENSIONS



(RS-20) Dimensions shown in millimeters

ORDERING GUIDE

Model ^{1, 2}	No. of Inputs, V _{DD1} Side	No. of Inputs, V _{DD2} Side	Maximum Data Rate (Mbps)	Maximum Propagation Delay, 3.3 V	Output Default State	Temperature Range	Package Description	Package Option
ADuM1240ARZ	2	0	2	180	High	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1240ARZ-RL7	2	0	2	180	High	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1240ARSZ	2	0	2	180	High	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1240ARSZ-RL7	2	0	2	180	High	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1241ARZ	1	1	2	180	High	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1241ARZ-RL7	1	1	2	180	High	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1241ARSZ	1	1	2	180	High	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1241ARSZ-RL7	1	1	2	180	High	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1245ARZ	2	0	2	180	Low	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1245ARZ-RL7	2	0	2	180	Low	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1245ARSZ	2	0	2	180	Low	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1245ARSZ-RL7	2	0	2	180	Low	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1246ARZ	1	1	2	180	Low	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1246ARZ-RL7	1	1	2	180	Low	-40°C to +125°C	8-Lead SOIC_N	R-8
ADuM1246ARSZ	1	1	2	180	Low	-40°C to +125°C	20-Lead SSOP	RS-20
ADuM1246ARSZ-RL7	1	1	2	180	Low	-40°C to +125°C	20-Lead SSOP	RS-20

¹ Z = RoHS Compliant Part. ² Tape and reel is available. The addition of the -RL7 suffix indicates that the product is shipped on 7" tape and reel.

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